GOODWORK

10N65

650V N-Channel MOSFET

Features:

Low Intrinsic Capacitances.

Excellent Switching Characteristics.

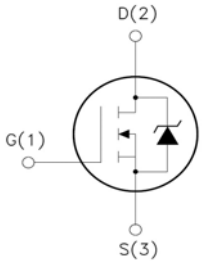
Extended Safe Operating Area.

Unrivalled Gate Charge :Qg=35nC (Typ.).

BVDSS=650 V,I_D=10A

$_{DS}$(on) : 0.95Ω (Max) @V_G=10V

100% Avalanche Tested

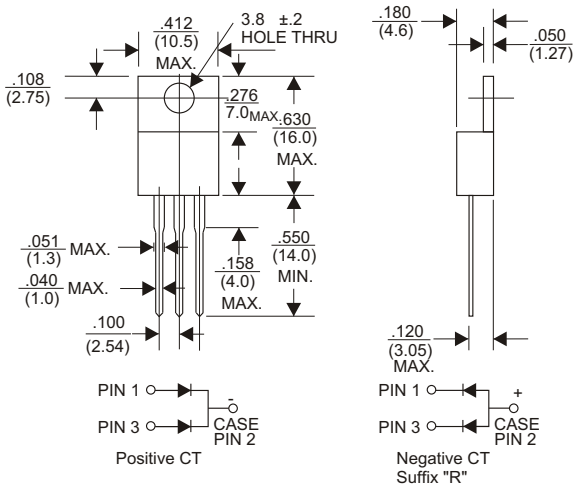


1.Gate (G)

2.Drain (D)

3.Sourse (S)

TO-220AB



Dimensions in inches and (millimeters)

Absolute Maximum Ratings (Ta=25℃ unless otherwise noted)

Sy mbol	Parameter		Value	Unit
V_{DSS}	Drain-Source Voltage		650	V
I_D	Drain Current	T_j=25℃	10	A
		T_j=100℃	6.7	
V_{GSS}	Gate-sourceVoltage		±30	V
E_{AS}	Single Pulse Avalanche Energy (note1)		380	mJ
I_{AR}	Avalanche Current (note2)		10	A
P_D	Power Dissipation (Tj=25℃)		65	W
T_j	Junction Temperature(Max)		150	℃
T_{stg}	Storage Temperature		-55~+150	℃
TL	Maximum lead temperature for soldering purpose,1/8’ from case for 5 seconds		300	℃

Thermal Characteristics

Sy mbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance,Junction to Case	-	2.4	℃/W
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient	-	62.5	℃/W

10N65

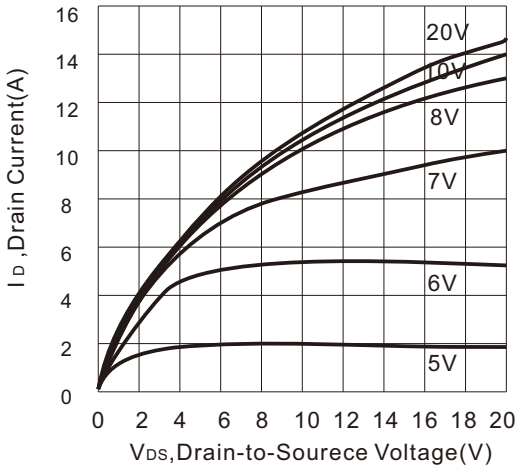
Electrical Characteristics (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250μA , V_{GS}=0	650	-	-	V
△BVDSS/△TJ	Breakdown Voltage Temperature Coefficient	I_D=250μA ,Reference to 25℃	-	0.67	-	V/℃
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=650V, V_{GS}=0V	-	-	10	μA
		V_{DS}=520V, Tj=125℃			100	
I_{GSSF}	Gate-body leakage Current, Forward	V_{GS}=+30V, V_{DS}=0V	-	-	100	nA
I_{GSSR}	Gate-body leakage Current, Reverse	V_{GS}=-30V, V_{DS}=0V	-	-	-100	
On Characteristics						
$V_{GS(TH)}$	Date Threshold Voltage	I_D=250μA,V_{DS}=V_{GS}	2	-	4	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	I_D=5.0A,V_{GS}=10V	-	0.8	0.95	Ω
Dynamic Characteristics						
Ciss	Input Capacitance	V_{DS}=25V , V_{GS}=0 , f=1.0MHz	-	1500	-	pF
Coss	Output Capacitance		-	194	-	
Crss	Reverse Transfer Capacitance		-	18	-	
Switching Characteristics						
Td(on)	Turn-On Delay Time	V_{DD}=325V , I_D=10A R_G=25Ω (Note 3,4)	-	23		nS
Tr	Turn-On Rise Time			15		
Td(off)	Turn-Off Delay Time		-	90		
Tf	Turn-Off Rise Time		-	30		
Qg	Total Gate Charge	V_{DS}=520V,V_{GS}=10V , I_D=10A (Note3,4)	-	35		nC
Qgs	Gate-Source Charge			7	-	
Qgd	Gate-Drain Charge			18	-	
Drain-Source Diode Characteristics and Maximum Ratings						
Is	Max. Diode Forward Current	-		- -	10	A
I_{SM}	Max. Pulsed Forward Current	-		- -	40	
V_{SD}	Diode Forward Voltage	I_D=10A	-	-	1.4	V
Trr	Reverse Recovery Time	I_S=10A,V_{GS}=0V diF/dt=100A/μs (Note3)	-	320	-	nS
Qrr	Reverse Recovery Charge		-	4. 2	-	μC

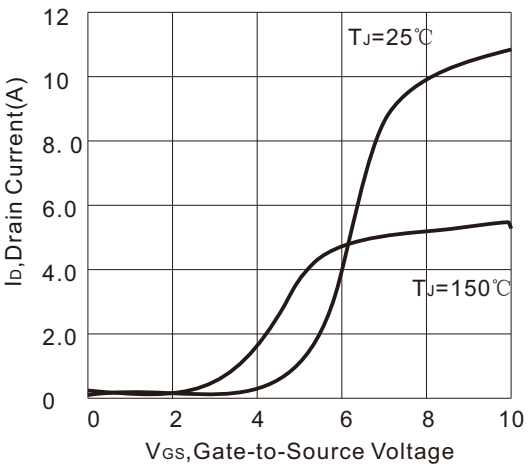
Notes : 1, L=0.5mH, IAS= 10A, VDD=50V, RG=25Ω , Starting TJ =25℃
2, Repetitive Rating : Pulse width limited by maximum junction temperature
3, Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
4, Essentially Independent of Operating Temperature

RATING AND CHARACTERISTIC CURVES (10N65)

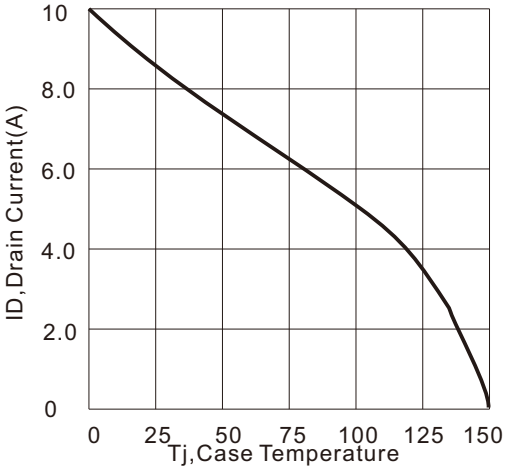
Output Characteristics



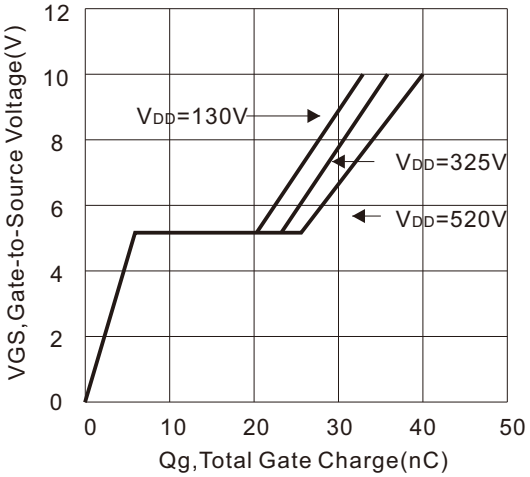
Transfer Characteristics



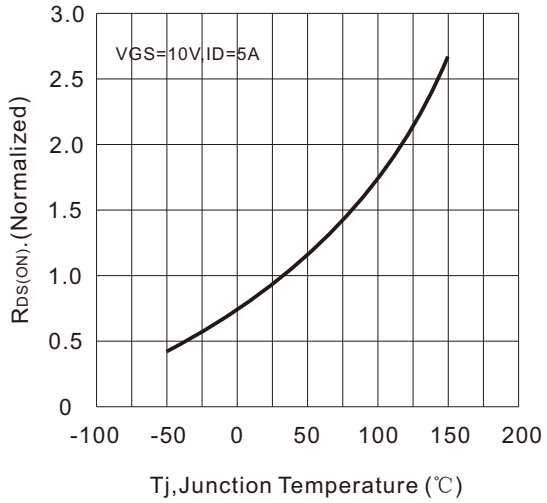
Drain Current VS.Temperature



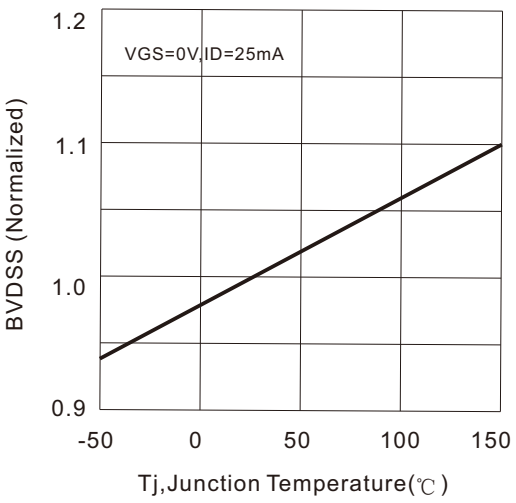
Gate Charge



On-Resistance vs. Junction Temperature

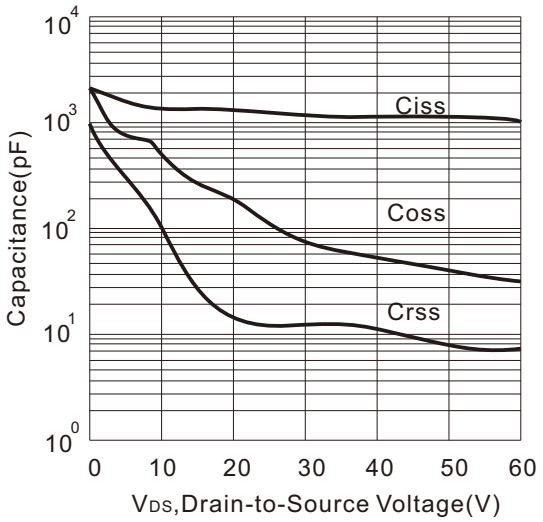


BVDSS Variation VS.Temperature

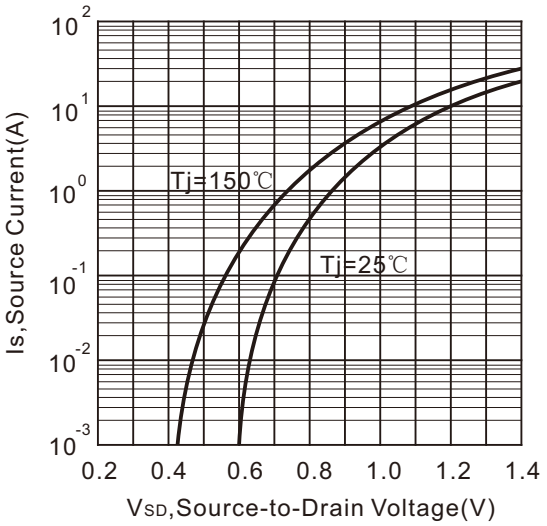


RATING AND CHARACTERISTIC CURVES (10N65)

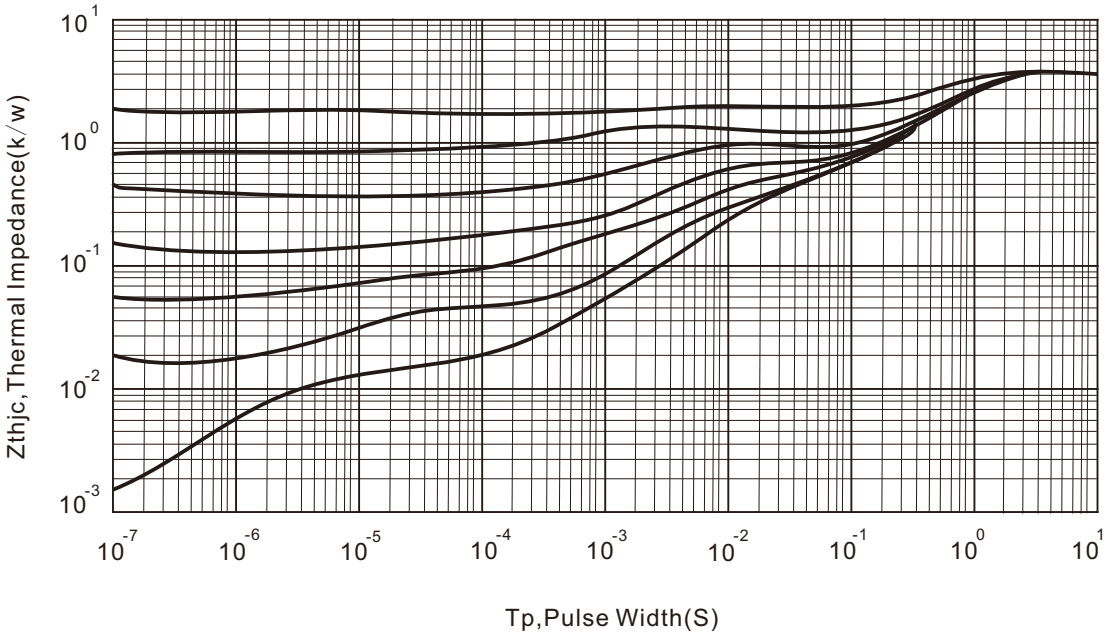
Capacitance



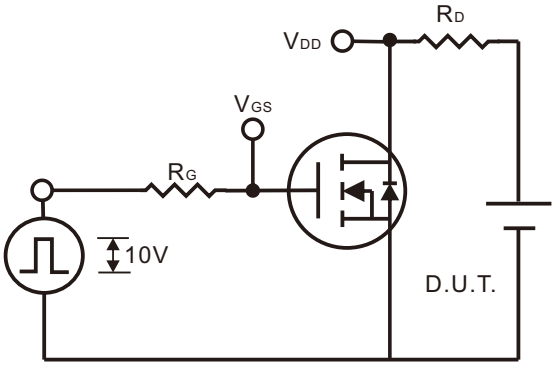
Body Diode Forward Voltage



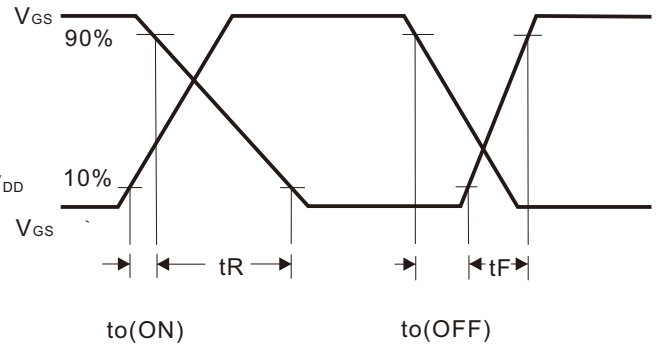
Transisent Thermal Impedance



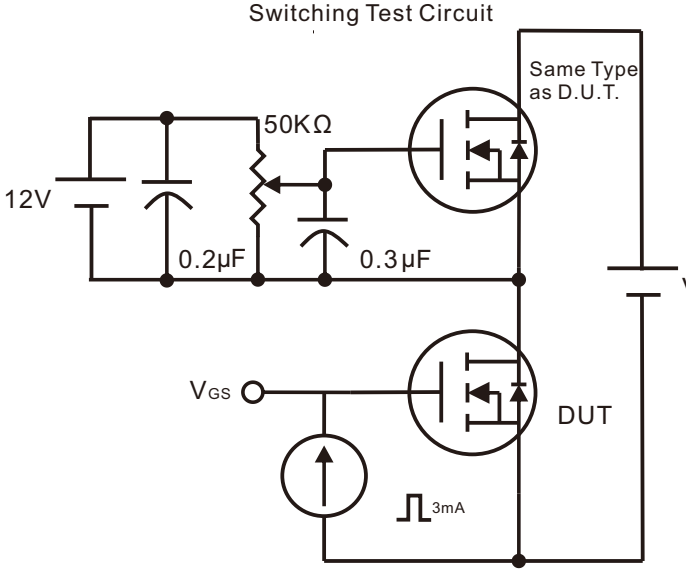
Gate Charge Test Circuit & Waveform



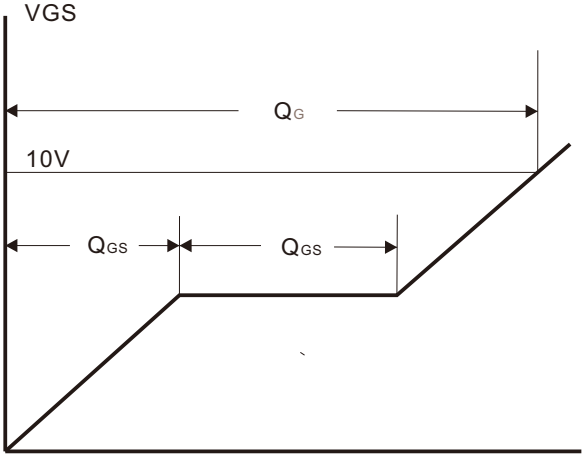
Switching Test Circuit



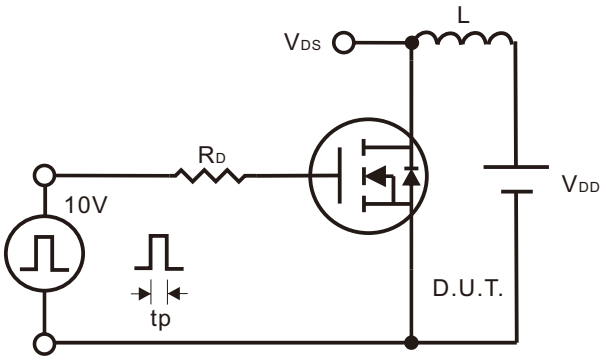
Switching Waveforms



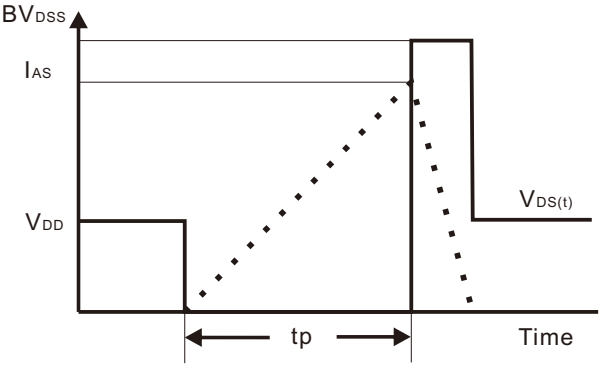
Gate Charge Test Circuit



Gate Charge Waveform

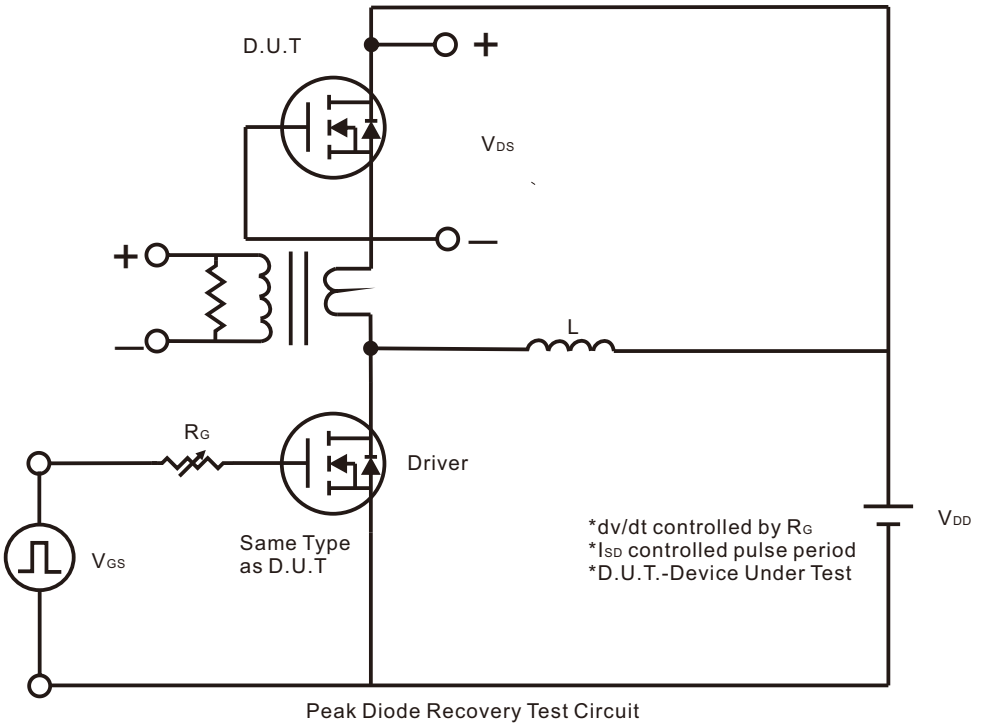


Unclamped Inductive Switching Test Circuit

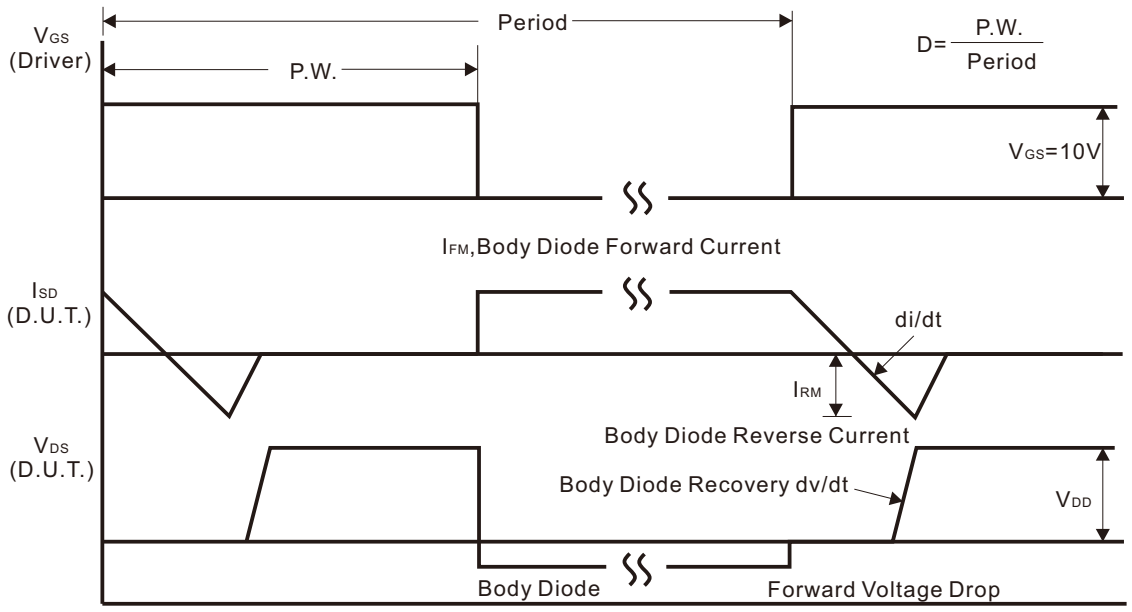


Unclamped Inductive Switching Waveforms

Peak Diode Recovery **dv/dt** Test Circuit & W**aveform**



Peak Diode Recovery Test Circuit



Peak Diode Recovery dv/dt Waveforms